

Docket No. 242330US2S/shb

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



IN RE APPLICATION OF: Kentaro NAKAJIMA

SERIAL NO: 10/653,976

GAU:

FILED: September 4, 2003

EXAMINER:

FOR: MAGNETIC MEMORY DEVICE

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS  
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- Each item of information contained in this information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,  
MAIER & NEUSTADT, P.C.



Marvin J. Spivak

Registration No. 24,913

Joseph A. Scafetta, Jr.  
Registration No. 26,803

Customer Number

22850

Tel. (703) 413-3000  
Fax. (703) 413-2220  
(OSMMN 05/03)

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**STATEMENT OF RELEVANCY**

**Reference AA (US 6,429,044) on Form 1449:**

Figure 2 of this document is similar to Figure 5 of the present application. However, the function explained in this document is quite different from our invention.

**Reference AB (US 5,939,772) on Form 1449:**

This document discloses a shield package for external magnetic field. However, the function and the structure are quite different from our invention.



Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 242330US2S	SERIAL NO. 10/653,976		
LIST OF REFERENCES CITED BY APPLICANT		APPLICANT Kentaro NAKAJIMA					
		FILING DATE September 4, 2003		GROUP			
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA	6,429,044	08/06/2002	M. TUTTLE			
	AB	5,939,772	08/17/1999	A. T. HURST, et al.			
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						
<b>FOREIGN PATENT DOCUMENTS</b>							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION		
	AO				YES	NO	
	AP						
	AQ						
	AR						
	AS						
	AT						
	AU						
	AV						
<b>OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)</b>							
	AW	R. SCHEUERLEIN, et al., IEEE International Solid-State Circuits Conference, ISSCC 2000 / Session 7/ TD: Emerging Memory & Device Technologies / Paper 7.2, pages 128-129, "TA 7.2 A 10ns READ AND WRITE NON-VOLATILE MEMORY ARRAY USING A MAGNETIC TUNNEL JUNCTION AND FET SWITCH IN EACH CELL", 2000					
	AX	M. SATO, et al., IEEE Transactions on Magnetics, vol. 33, no. 5, pages 3553-3555, "SPIN-VALVE-LIKE PROPERTIES AND ANNEALING EFFECT IN FERROMAGNETIC TUNNEL JUNCTIONS", September 1997					
	AY	M. SATO, et al., Jpn. J. Appl. Phys, vol. 36, part 2, no. 2B, pages L200-L201, "SPIN-VALVE-LIKE PROPERTIES OF FERROMAGNETIC TUNNEL JUNCTIONS", February 15, 1997					
	AZ	K. INOMATA, et al., Jpn. J. Appl. Phys, vol. 36, part 2, no. 10B, pages L 1380-L 1383, "SPIN-DEPENDENT TUNNELING BETWEEN A SOFT FERROMAGNETIC LAYER AND HARD MAGNETIC NANOSIZE PARTICLES", October 15, 1997			<input type="checkbox"/> Additional References sheet(s) attached		
Examiner					Date Considered		
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							